

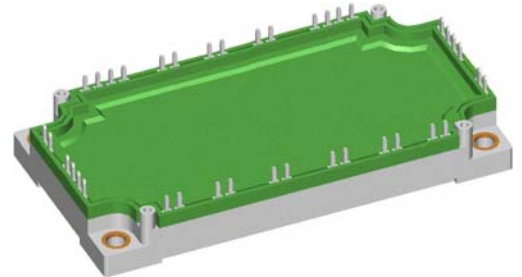
XPT IGBT Module

3~ Rectifier	Brake Chopper	3~ Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 135 \text{ A}$	$I_{C25} = 60 \text{ A}$	$I_{C25} = 85 \text{ A}$
$I_{TSM} = 700 \text{ A}$	$V_{CE(sat)} = 1.8 \text{ V}$	$V_{CE(sat)} = 1.8 \text{ V}$

6-Pack + 3~ Rectifier Bridge, half-controlled (high-side) & Brake Unit + NTC

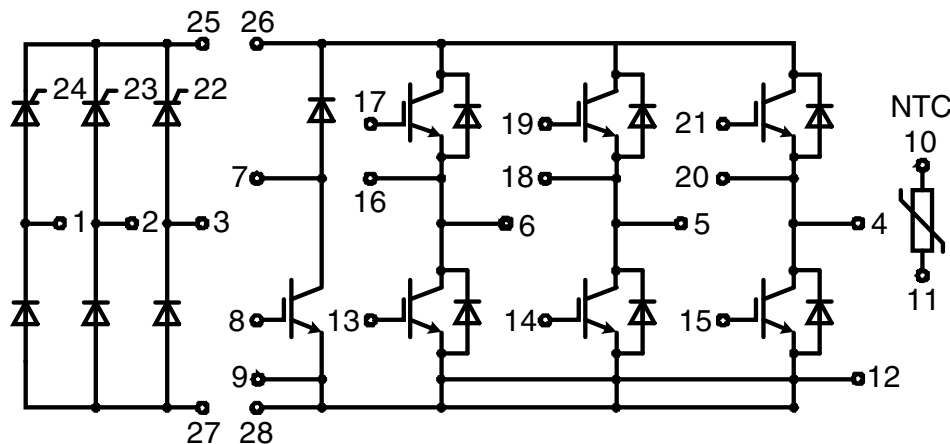
Part number

MIXA60WH1200TEH



Backside: isolated

E72873



Features / Advantages:

- Thyristor/Standard Rectifier for line frequency
- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_C
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package:

- Housing: E3-Pack
- International standard package
- RoHS compliant
- Isolation voltage: 3600 V~
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			20	mA
V_T	forward voltage drop	$I_T = 80\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.43	V
		$I_T = 160\text{ A}$				1.86	V
		$I_T = 80\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.42	V
		$I_T = 160\text{ A}$				1.97	V
I_{DAV}	bridge output current	$T_C = 80^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			135	A
		180° sine $d = 1/3$					
V_{T0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.85	V
r_T	slope resistance					7.1	m Ω
R_{thJC}	thermal resistance junction to case					0.65	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				190	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			700	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			755	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			595	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			645	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.45	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.37	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.77	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.73	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		32		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$	repetitive, $I_T = 150\text{ A}$			100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
		$I_G = 0.45\text{ A}; V_D = 2/3 V_{DRM}$	non-repet., $I_T = 45\text{ A}$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			78	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					5	mA
I_L	latching current	$t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			450	mA
		$I_G = 10\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			100	mA
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 20\text{ A}; V_D = 2/3 V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$		150		μs
				$di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 15\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$			

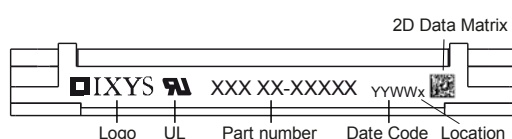
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Brake IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{GES}	max. DC gate voltage					± 20	V
V_{GEM}	max. transient collector gate voltage					± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$				60	A
I_{C80}		$T_C = 80^{\circ}\text{C}$				40	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				195	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 35\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.8	2.1	V
			$T_{VJ} = 125^{\circ}\text{C}$		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 1.5\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.4	5.9	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2.1	mA
			$T_{VJ} = 125^{\circ}\text{C}$		0.1		mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$				500	nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 35\text{ A}$			106		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 35\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		70		ns
t_r	current rise time				40		ns
$t_{d(off)}$	turn-off delay time				250		ns
t_f	current fall time				100		ns
E_{on}	turn-on energy per pulse				3.8		mJ
E_{off}	turn-off energy per pulse				4.1		mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 27\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$				
I_{CM}		$V_{CEK} = 1200\text{ V}$				105	A
SCSOA	short circuit safe operating area						
t_{sc}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			10	μs
I_{SC}	short circuit current	$R_G = 27\ \Omega$; non-repetitive			140		A
R_{thJC}	thermal resistance junction to case					0.64	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W
Brake Diode							
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			44	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			29	A
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.20	V
			$T_{VJ} = 125^{\circ}\text{C}$			1.95	V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			0.1	mA
			$T_{VJ} = 125^{\circ}\text{C}$			0.15	mA
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $-di_F/dt = 600\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		3.5		μC
I_{RM}	max. reverse recovery current				30		A
t_{rr}	reverse recovery time				350		ns
E_{rec}	reverse recovery energy				0.9		mJ
R_{thJC}	thermal resistance junction to case					1.2	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W

Inverter IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{GES}	max. DC gate voltage					± 20	V
V_{GEM}	max. transient collector gate voltage					± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$				85	A
I_{C80}		$T_C = 80^{\circ}\text{C}$				60	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				290	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 55\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.8	2.1	V
			$T_{VJ} = 125^{\circ}\text{C}$		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 2\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.4	5.9	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			0.5	mA
			$T_{VJ} = 125^{\circ}\text{C}$		0.2		mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$				500	nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 55\text{ A}$			165		nC
$t_{d(on)}$	turn-on delay time	} inductive load $V_{CE} = 600\text{ V}; I_C = 55\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$		70		ns
t_r	current rise time				40		ns
$t_{d(off)}$	turn-off delay time				250		ns
t_f	current fall time				100		ns
E_{on}	turn-on energy per pulse				4.5		mJ
E_{off}	turn-off energy per pulse				5.5		mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$				
I_{CM}		$V_{CEmax} = 1200\text{ V}$				150	A
SCSOA	short circuit safe operating area	$V_{CEmax} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$				
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V}$				10	μs
I_{SC}	short circuit current	$R_G = 15\text{ }\Omega$; non-repetitive			200		A
R_{thJC}	thermal resistance junction to case					0.43	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W
Inverter Diode							
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			88	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			59	A
V_F	forward voltage	$I_F = 60\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.20	V
			$T_{VJ} = 125^{\circ}\text{C}$		1.95		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			0.3	mA
			$T_{VJ} = 125^{\circ}\text{C}$		1.2		mA
Q_{rr}	reverse recovery charge	} $V_R = 600\text{ V}$ $-di_F/dt = 1200\text{ A}/\mu\text{s}$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		8		μC
I_{RM}	max. reverse recovery current				60		A
t_{rr}	reverse recovery time				350		ns
E_{rec}	reverse recovery energy				2.5		mJ
R_{thJC}	thermal resistance junction to case					0.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W

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Package E3-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			300	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				270		g
M_D	mounting torque		3		6	Nm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm



Part number

M = Module
 I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 60 = Current Rating [A]
 WH = 6-Pack + 3~ Rectifier Bridge, half-controlled (high-side) & Brake Unit
 1200 = Reverse Voltage [V]
 T = Thermistor \ Temperature sensor
 EH = E3-Pack

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MIXA60WH1200TEH	MIXA60WH1200TEH	Box	5	509622

Similar Part	Package	Voltage class
MIXA60WB1200TEH	E3-Pack	1200

Temperature Sensor NTC

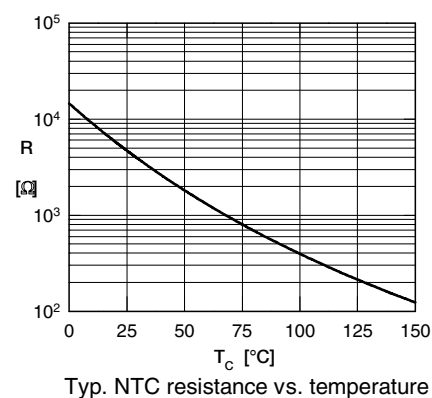
Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	kΩ
$B_{25/50}$	temperature coefficient			3375		K

Equivalent Circuits for Simulation

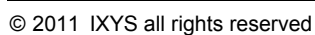
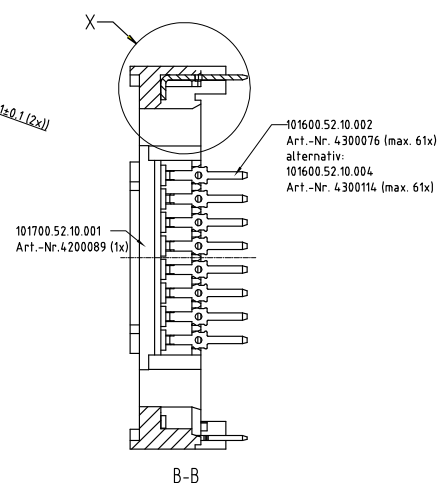
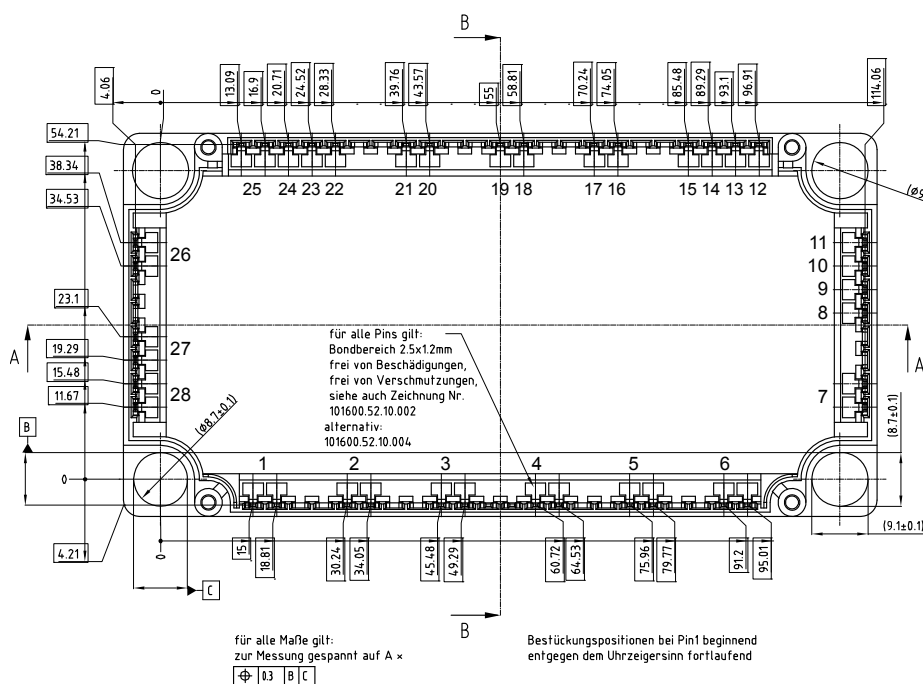
* on die level

$T_{VJ} = 150^\circ\text{C}$

		Rectifier	Brake IGBT	Brake Diode	Inverter IGBT	Inverter Diode
V_0	threshold voltage	0.85	1.1	1.2	1.1	1.22
R_0	slope resistance *	3.9	40	27	25.1	13



Technical drawing showing a cross-section of a mechanical assembly. A pin (Pins) is shown inserted into a dovetail (Pinvorderekte) joint. The drawing includes a scale of 5:1 and a dimension of 90° ± 1 mm. A note indicates that the pins are not to be used between dovetail joints.



Rectifier

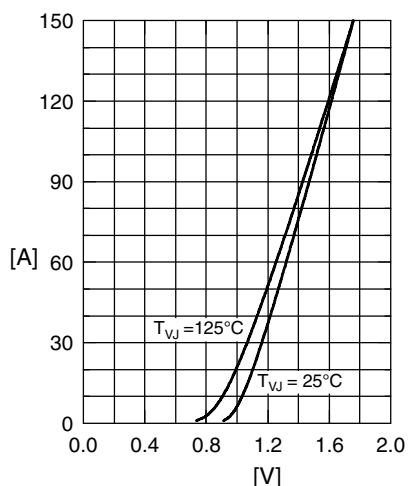


Fig.1 Forward current versus voltage drop per diode

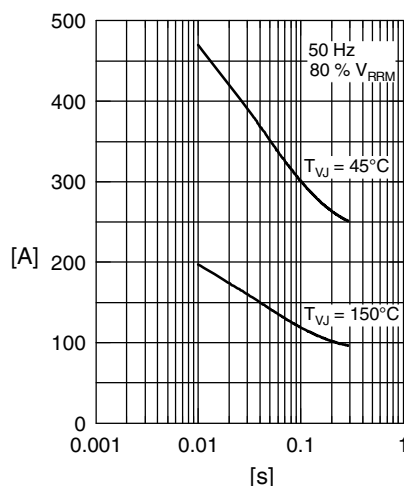


Fig.2 Surge overload current

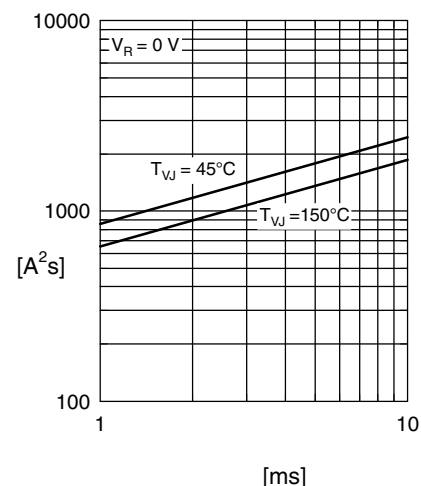


Fig.3 I^2t versus time per diode

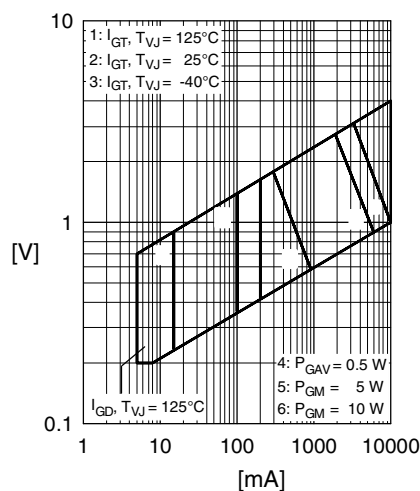


Fig. 4 Gate trigger characteristics

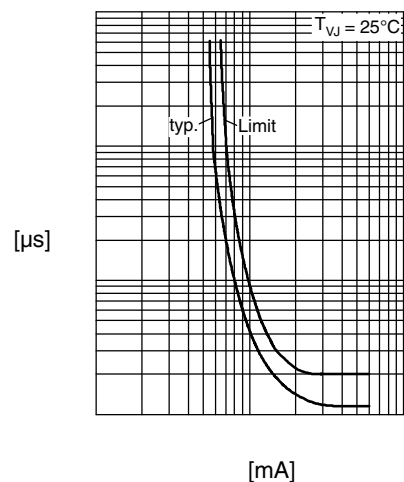


Fig. 5 Gate trigger delay time

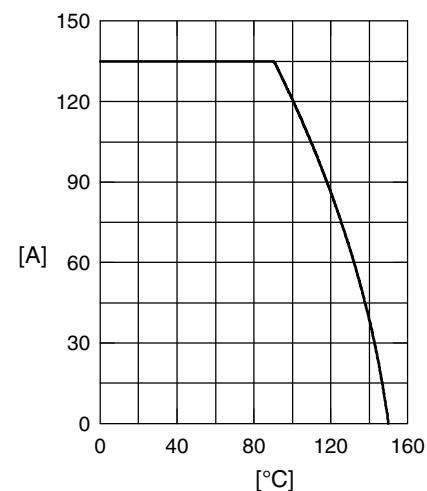


Fig. 6 Max. forward current versus case temperature

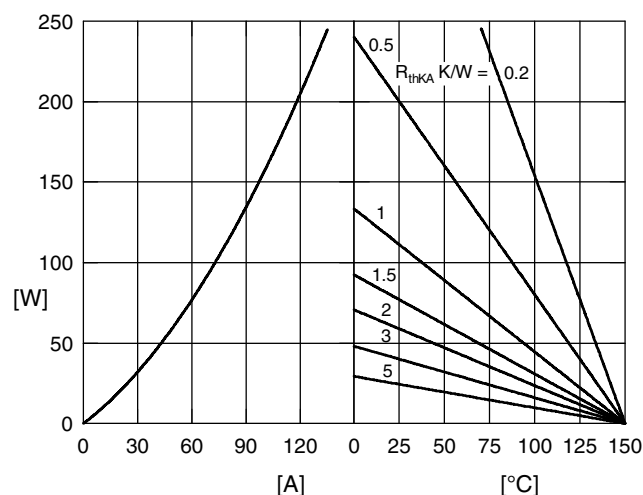


Fig.7 Power dissipation versus direct output current and ambient temperature, sine 180°

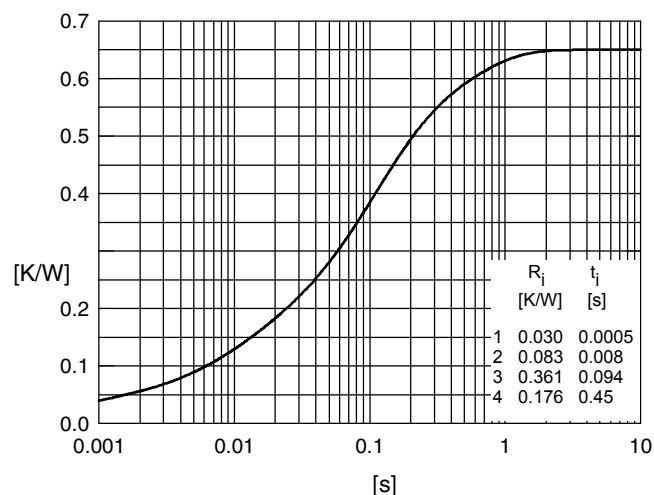


Fig. 8 Transient thermal impedance junction to case

Brake IGBT

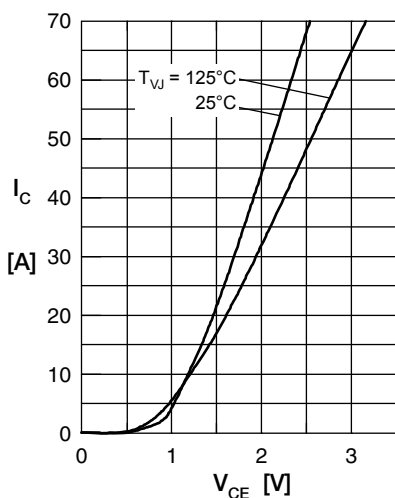


Fig. 1 Typ. output characteristics

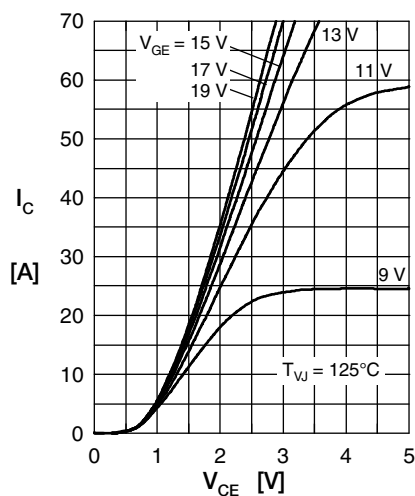


Fig. 2 Typ. output characteristics

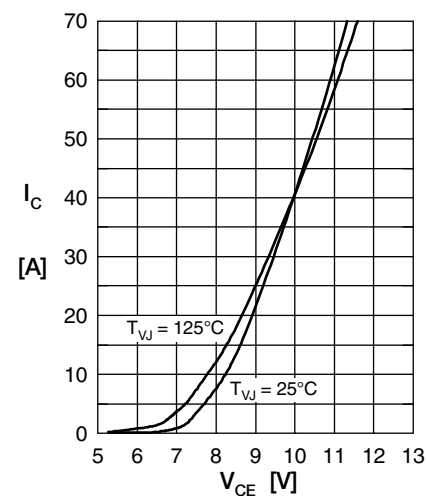


Fig. 3 Typ. transfer characteristics

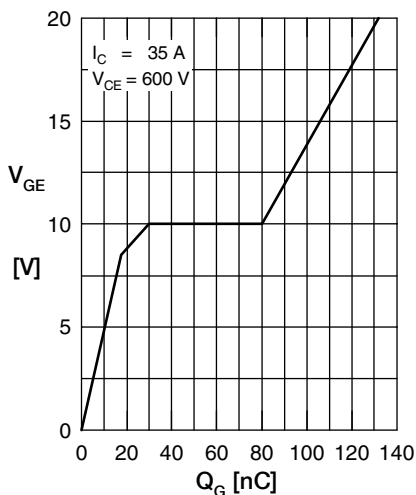


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

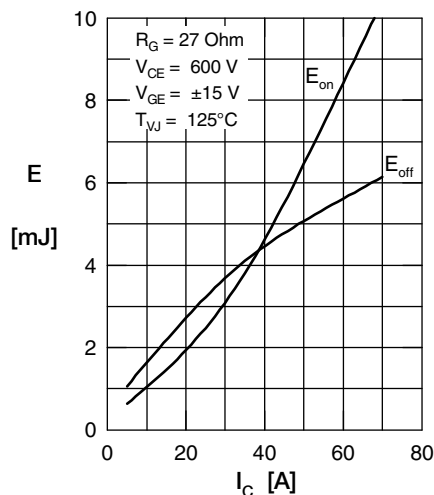


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

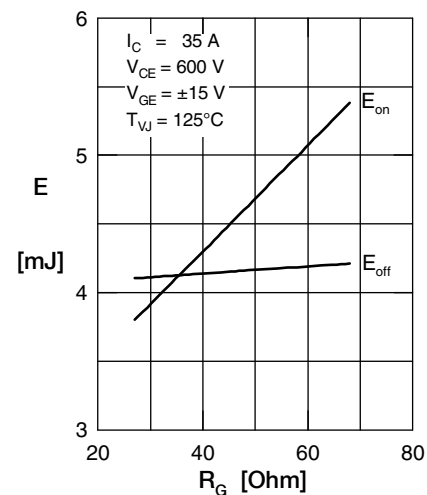


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

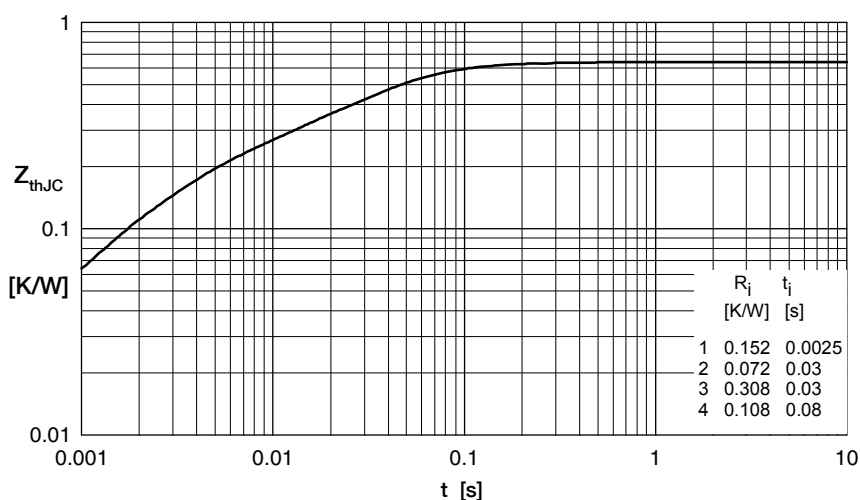


Fig. 7 Transient thermal impedance junction to case

Brake Diode

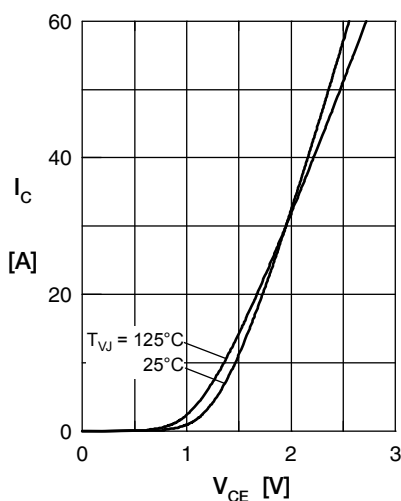


Fig. 1 Typ. Forward current versus V_F

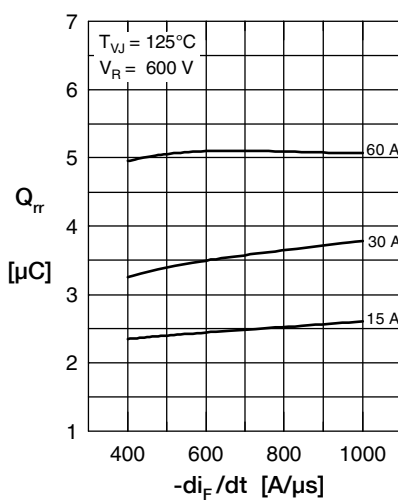


Fig. 2 Typ. reverse recovery charge Q_{rr} versus di/dt

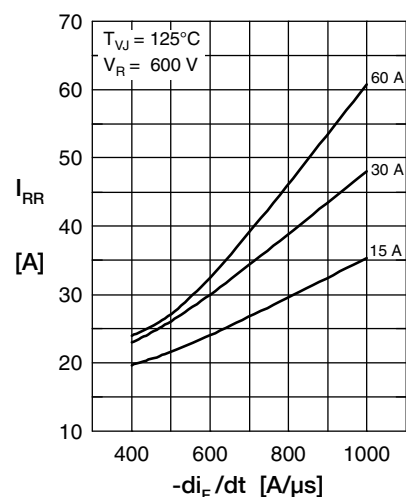


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

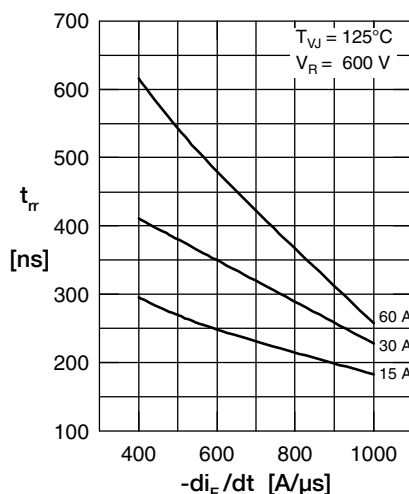


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

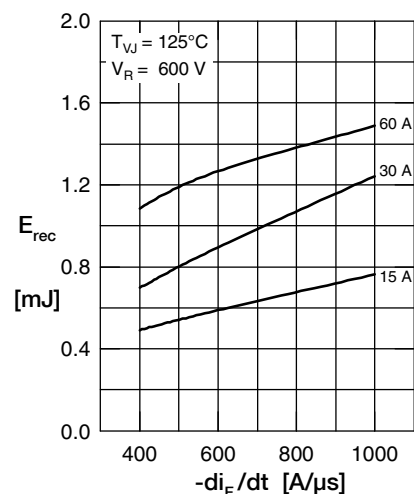


Fig. 6 Typ. recovery energy E_{rec} versus $-di/dt$

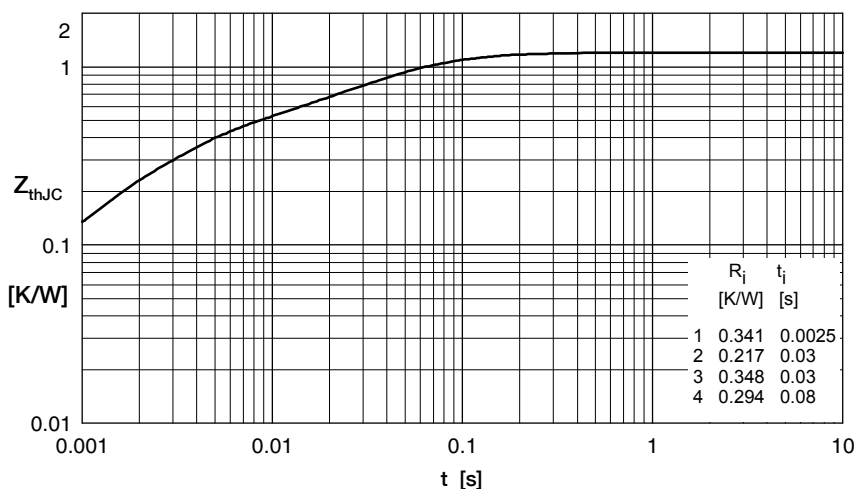


Fig. 7 Transient thermal impedance junction to case

Inverter IGBT

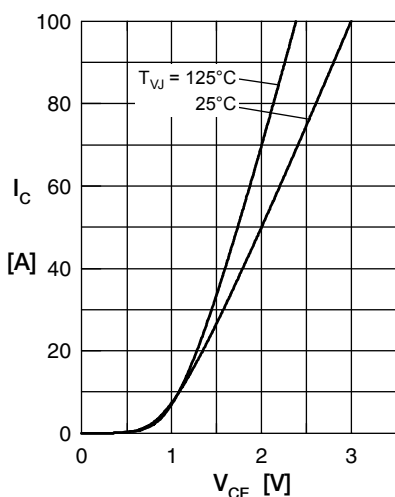


Fig. 1 Typ. output characteristics

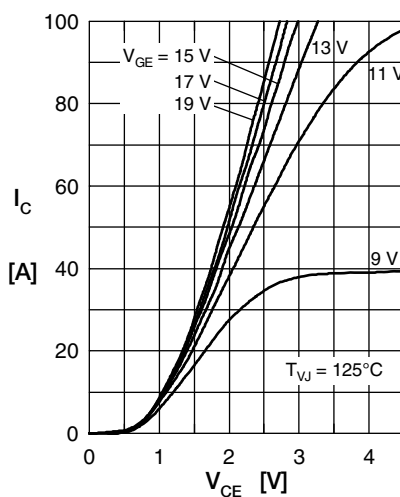


Fig. 2 Typ. output characteristics

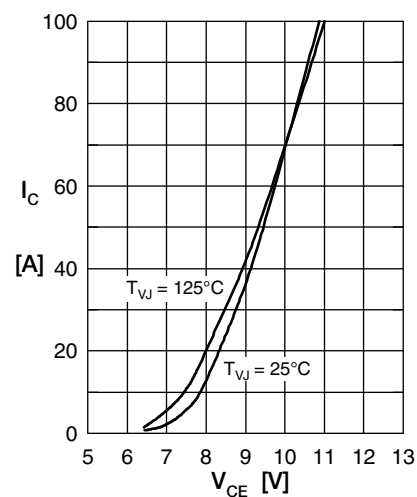


Fig. 3 Typ. transfer characteristics

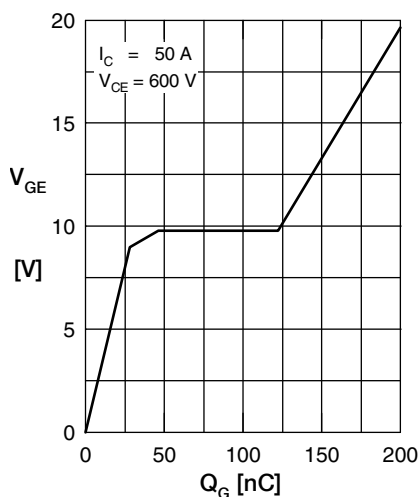


Fig. 4 Dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

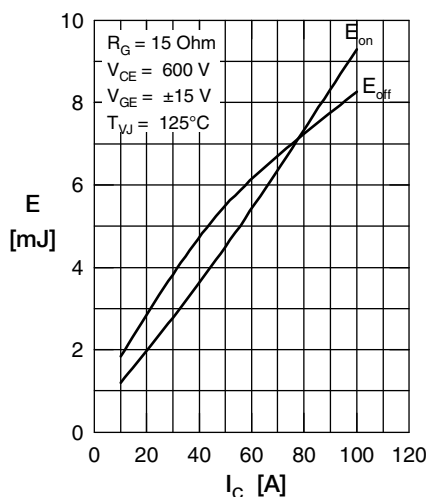


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

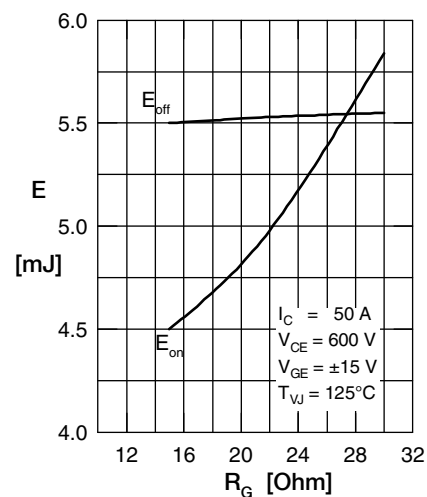


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{fr} versus di_F/dt

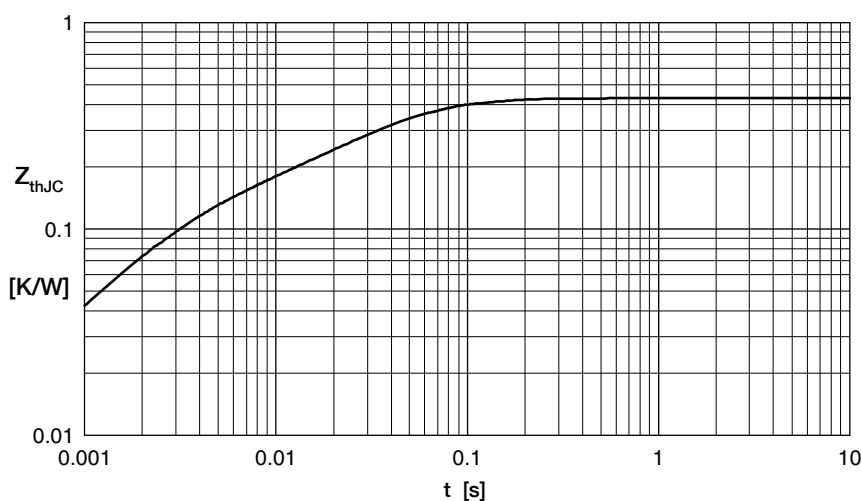


Fig. 7 Transient thermal impedance junction to case

Inverter Diode

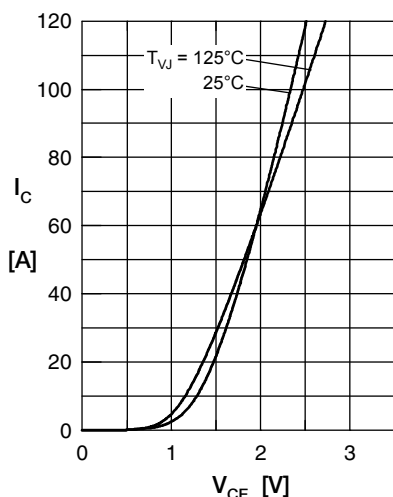


Fig. 1 Typ. Forward current versus V_F

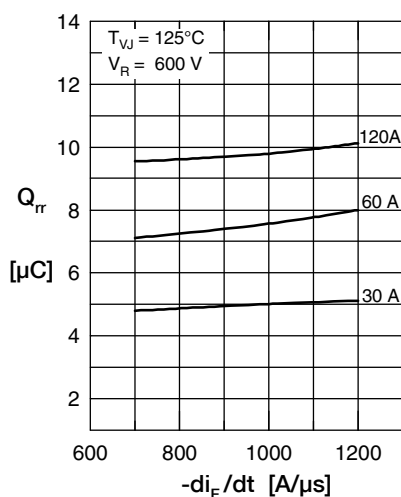


Fig. 2 Typ. reverse recovery charge Q_{rr} versus di/dt

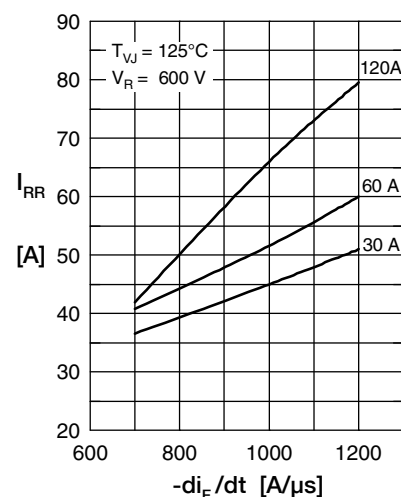


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

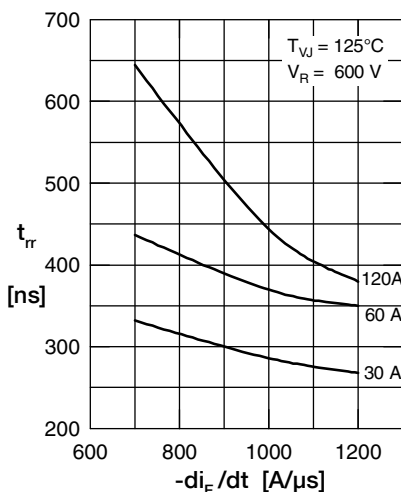


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

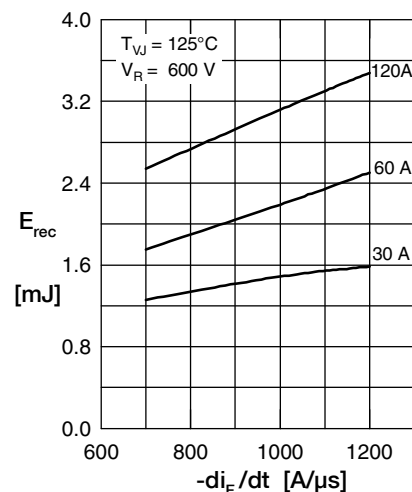


Fig. 6 Typ. recovery energy E_{rec} versus $-di/dt$

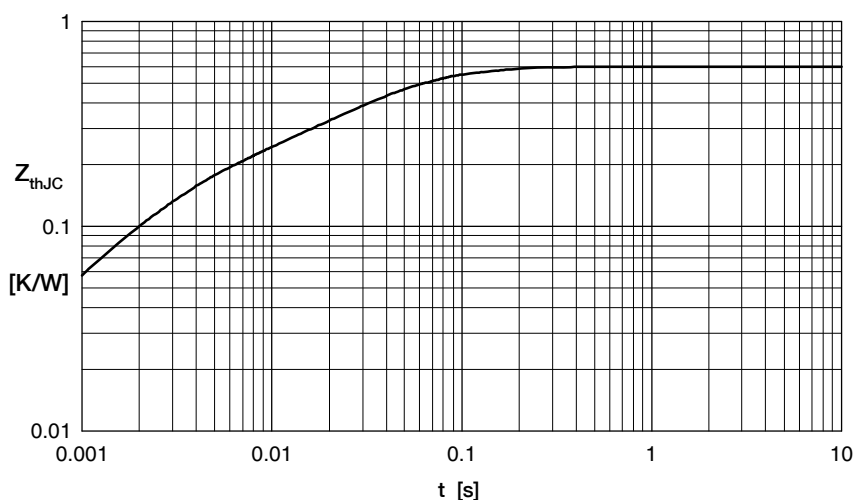


Fig. 7 Transient thermal impedance junction to case